## Spin Halle ects in di usive norm alm etals.

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We consider spin and charge ow in normal metals. We employ the Keldysh formalism to not transport equations in the presence of spin-orbit interaction, interaction with magnetic impurities, and non-magnetic impurity scattering. Using the quasiclassical approximation, we derive disusion equations which include contributions from skew scattering, side-jump scattering and the anomalous spin-orbit induced velocity. We compute the magnitude of various spin Halle ects in experimental relevant geometries and discuss when the discrept scattering mechanisms are important.

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### I. INTRODUCTION

Spin ow in nanostructures has recently attracted considerable interest in the scientic community  $^{1,2,3}$ . The vision of magnetoelectronics and spintronics is to inject, manipulate and detect spins in nanostructures which can give new functionality in electronic devices. The spin ow can be controlled by e.g. external electric or magnetic elds.

A Hallvoltage builds up perpendicularly to the current ow under an applied magnetic eld in normal metals due to the Lorentz force. The Hall voltage increases with applied magnetic eld. Magnetoelectronic circuits are often realized by using ferrom agnets that can spin polarize the current ow. In ferrom agnets, there is an anom alous Hall voltage proportional to the magnetization, e.g. a transverse charge potential, even in the absence of an applied magnetic eld. The anomalous Halle ect is caused by the spin-orbit interaction, which correlates the momentum of the electron with its spin. This causes an dependence of the electron ow with the relative angle between its direction and the non-zero magnetic order param eter in ferrom agnets. 4,5,6 In ferrom agnetic m etals, spin-orbit interaction is also a source of crystalline magnetic anisotropy energies since the spin-orbit interaction couples the magnetization with the crystal structure.

The scattering mechanisms responsible for the anomalous Hall e ect are skew scattering and side-jump scattering<sup>8</sup> as well as the anom alous velocity operator due to spin-orbit interaction and impurity scattering. A schematic picture of the skew scattering mechanism is shown in Fig. 1. After scattering of the impurity potential, there is a spin-dependent probability di erence, represented by small angles, of the electron trajectories. This leads e.g. to a slightly larger chance that electrons with spin up moves upwards and electrons with spin down m oves downwards after scattering. The side-jum pm echanism is also caused by the combined spin-orbit and impurity scattering, see Fig. 2. After scattering of the impurity, a sm all "side-jum p", develops between the trajectories of electrons with spin up and down far away from the scattering center. Additionally, the spin-orbit interaction does not commute with the electron momentum operator. This leads to an anom alous velocity operator

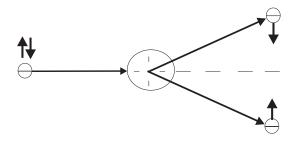


FIG. 1: Schem atic picture of the skew scattering m echanism. An incident electron w ith spin up (down) scatters preferrably w ith a postive (negative) angle.

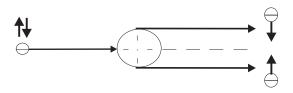


FIG. 2: Schem atic picture of the side-jump m echanism. The trajectory of the outgoing electrons is shifted to the upper (lower) side the scattering center at large distances for spin up (down) states.

that can contribute to the Halle ects, as well.

Spin-orbit scattering is also important in nomalmetals. It is well known that it causes a loss of spin coherence. Hirsch predicted the existence of a novel spin Hall e ect<sup>5</sup> analogues to the anomalous Hall e ect in ferromagnets and developed a phenomenological theory for the e ect. In the absence of spin-orbit scattering, electrons with spin-up and spin-down scatter equally on non-magnetic impurities. However, as seen above, for nonzero spin-orbit interaction, when a current passes through the sample an imbalance between left-moving and right-moving particles is established, and an accompanying transverse spin accumulation potential builds up in the system.

Zhang computed this spin potential in the diusive transport regime, and found that it should be measurable<sup>9</sup>. He considered longitudinal transport in a thin normal metal lm, and computed the resulting transverse spin Hall voltage. In this regime, the spin-

accumulation is weak and he found that the spin Hall voltage is governed by the anomalous velocity operator. By using the framework developed by Hirsch and Zhang, elects of contact resistances on the spin Halle ect have also been considered 10.

Spin-orbit scattering is also important in nand p-doped semiconductors, where Rashba-type spin-orbit coupling 11 leads to interesting spin Hall e ects<sup>12,13,14,15,16,17</sup>,18,19,20,21,22,23,24,25,26 interesting case is spin transport in a two-dimensional electron system (2DES). The study of this e ect is controversial. The debate 16,17,19,20,21,22,24,27 is focused on whether or not the spin Hall conductivity has a universal value  $_{SH} = e= (8 \text{ h})$  and in what regime this result is applicable. Our study is complementary to these studies of spin Hall e ects in semiconductors. In our normal metal case, the extrinsic<sup>28</sup> spin Hall e ects arise due to the spin-orbit at impurities. sem iconductors, spin-orbit interaction can be important even in ballistic system s29, in the absence of impurities, for system s with broken spatial inversion symmetry.

In this work, we derive the spin Halle ects in the presense of spin di usion from the Eilenberger equation 30 in presence of spin-orbit coupling<sup>31</sup>, magnetic impurities and non-magnetic impurities. We use the Keldysh Green function technique in the quasiclassical approximation. Our calculations go beyond the assumptions in Ref. 9, which only included e ects of the anom alous velocity operator, in that we rigorously derive di usion equations that also include e ects of skew scattering and side-jum p scattering. Our results agree with the results by Zhang in the lim it he considered, where skew scattering and sidejum p scattering can be disregarded. We also consider spin and charge transport in normal metals in another transport regim e, phenom enologically treated by Hirsch, when norm alm etals are biased by ferrom agnets, in which spins accumulate in the normalmetaleven in the absence of the spin-orbit interaction. We demonstrate that in this regime, skew scattering and side-jump scattering cannot be disregarded, and compute the spin Halland spin-orbit induced charge Halle ects. In our analysis, we also consider transport through ferrom agnet-norm alm etalinterfaces beyond the assumptions in Ref. 10 by using the boundary conditions obtained within magneto-electronic circuit theory, which is necessary in dealing with noncollinear spin and magnetization directions. Finally, our form alism also explicitly incorporates the e ects of scattering o magnetic impurities, which can reduce the spin Halle ects.

Our paper is organized in the following way. In the next section, Section II, we outline our starting point microscopic Hamiltonian, and explain the diusion equations for spin and charge ow that we have obtained rigorously by using the non-equilibrium Keldysh Green function approach in the quasi-classical approximation. We compute from the diusion equations the spin Hall e ects in some relevant experimental geometries in Section III. Our derivation of the charge and spin diusion

equation is an important part of our work, and its details are given in Section IV . Finally, we give our conclusions in Section  $\rm V$  .

#### II. MODEL AND TRANSPORT EQUATIONS

We consider quasi-particles in a normal metal that interact with non-magnetic and magnetic impurities and include the spin-orbit interaction. The Hamiltonian of the system is

$$H = \frac{h^2}{2m} r^2 + V_{im p} + \hat{V}_{so} + \hat{V}_{sm} ; \qquad (1)$$

where we below will introduce the various terms. Im purity scattering is represented by the short-range potential

$$V_{\text{im p}} = X_{\text{i}} (r r_{i}); \qquad (2)$$

where  $r_i$  is the coordinate of the i-th impurity center and  $_i$  is the strength of the scattering potential. It is assumed that the scatterers are disordered so that <  $V_{\mbox{im}\ p}$  (r)>= 0 and <  $V_{\mbox{im}\ p}$   $(r)V_{\mbox{im}\ p}$   $(r^0)>=$   $(r-r^0)n^{-2}$ , where n is the impurity density and  $^2$  is the average uctuation of the scattering strengths.

The spin-orbit interaction is described by the  ${\tt H}\,{\tt am}\,\,{\tt il}\!\!-\!\!\!$  tonian,

$$\hat{V}_{so} = \frac{1}{2} \frac{1}{hk_F^2} (\hat{p} + h.c.;$$
 (3)

where  $\,$  is the dim ensionless spin-orbit coupling constant,  $k_F$  is the Ferm i wave number and h.c. denotes the hermitian conjugate.

M agnetic im purites are introduced by

$$\hat{V}_{sm} = V_{sm} (r)^{s} S (r); \qquad (4)$$

where  $V_{\text{sm}}$  (r) is the strength of the coupling of the itinerant electron spin to the spin of the magnetic impurity S (r).

We are interested in the transport properties of diusive system where the system size is much larger than the mean free path. A rigorous method to obtain the correct diusion equation is to start from a microscopic description using the non-equilibrium Keldysh formalism. We consequently employ the Keldysh approach with two approximations. First, we consider the quasiclassical approximation, which is valid on length scales much larger than the Fermiwavelength, Left Second, we use the diusion approximation which is valid when the system size is much larger than the mean free path, Left 1 =  $v_{\rm F}$ .

The full derivation of the di usion equation is an important part of the present paper, but it is technically complicated and in order to make the paper more easily accessible we delay its derivation to the interested readers in Section IV. First, we show and explain the spin and charge di usion equations as well as the expression

for the corresponding currents that we obtain. We introduce charge and spin-distributions  $_{\rm c}$  and  $_{\rm s}$ , so that the charge density and spin-density are

$$n(r) = N_{o(c)}(r);$$
  
 $s(r) = N_{o(c)}(r);$ 

where N  $_{\circ}$  is the density of states. A fler considerably algebra outlined in Section IV , we not that the resulting di usion equation for the charge distribution functions is  $\sin p \ln p$ 

$$r^2 = 0$$
: (5)

Sim ilarly, the spin-distribution for small spin-orbit interactions, 1, is governed by

$$Dr^{2}_{s} = \frac{1}{s} + \frac{1}{s}_{s}$$
 (6)

where D =  $\frac{1}{3}v_F^2$  is the di usion coe cient in terms of the Ferm i velocity  $v_F$  and the elastic scattering time , so is the spin- ip relaxation time due to the spin-orbit interaction,

$$\frac{1}{80} = \frac{8^{-2}}{9} \tag{7}$$

and  $_{\rm sm}$  is the spin- ip relaxation time due to magnetic impurities,

$$\frac{1}{sm} = \frac{8 \text{ n}_{sm} \text{ N}_{0} \text{S} (\text{S} + 1) \text{V}_{sm}^{2}}{3} :$$
 (8)

Here we have expressed the strength of the magnetic impurity potential from Eq. (4) in the momentum representation  $v_{\text{sm}}$ ,  $n_{\text{sm}}$  is the concentration of the magnetic impurities, and S is the spin of the impurity. Thus, both the diusion equations for charge and spin have the familiar form sused exensively in the literature for spin and charge transport.

Skew scattering, side-jum p scattering and e ects of the anom alous velocity operator are all contained in the expressions for the current. We not that the total 2 current in spin-space can be expressed as

$$\hat{j} = \hat{j}_0 + \hat{j}_{av} + \hat{j}_{ss} + \hat{j}_{si}; \tag{9}$$

where  $\hat{j}_o$  is the ordinary current without spin-orbit interaction,  $\hat{j}_{av}$  is the current due to the anom alous velocity operator,  $\hat{j}_{ss}$  is the current due to skew scattering and  $\hat{j}_{sj}$  is the current due to side-jump scattering. The full derivation of these currents is given in Section IV . The charge and spin currents can be obtained by the trace of Eq. (9) with the unit matrix and the Pauli matrices, respectively. In the limit of weak spin-orbit interaction (to lowest order in ), which is relevant for most normal metals, we compute the following contributions to the

current:

$$e_{j_0}^{\uparrow} = \frac{1}{2} \hat{l} r_{c} + r_{(s^{\uparrow})};$$
 (10)

$$e\hat{j}_{av} = \frac{h}{6m D} [r _{s} + ^{r} _{c}];$$
 (11)

$$e_{jsj}^{2} = \frac{1}{3} (r)_{s};$$
 (12)

$$\hat{e}_{ss} = ^(r_s); \qquad (13)$$

where =  $e^2N_0D$  is the conductivity. The anomalous current,  $\hat{j}_{av}$ , contributes both to the spin and charge current. Contributions from skew scattering and side-jum p scattering,  $\hat{j}_{ss}$  and  $\hat{j}_{sj}$ , only a ect the spin-current. The current contribution  $\hat{j}_{sj}$  depends on the divergence of the spin accumulation in the direction of the current for any spin, which is the side-jump mechanism. The current contribution  $\hat{j}_{ss}$  arises from skew scattering. If we com pare our results with Zhang<sup>9</sup>, we see that in addition to the contributions from the anomalous velocity operator we include terms representing skew scattering and side-jum p scattering. We demonstrate below that these additional contributes could correctly be disregarded in the geometry in Ref. 9, but that they the dominate spin Halle ects in other systems. We also derive expressions for the total current in case of arbitary IV).

#### III. EXPERIMENTAL IMPLICATION.

Let us now employ our theory to calculate the magnitude of the spin Halle ect in experimental relevant geom etries. For simplify, we will consider the cases with small spin-orbit interaction ( 1), where the small expressions for the current, (10), (11), (12) and (13), are valid

## A. Thin metallic lm.

We consider set a pure normal metal as considered in Ref. 9 and shown in Fig. 3. A thin Im normal metal of length L and width d is attached with perfect contacts with zero resistance to a left reservoir with local chemical potential L and a right reservoir with local chemical potential R. In a pure normal metal system, there is no spin-accumulation in the limit ! 0. That means that the spin-accumulation is small, being induced by the spin-orbit interaction. From (11), (12) and (13) we thus see that contributions from the skew scattering and sidejump scattering to the current are of a higher order in the spin-orbit scattering than the anomalous current and can be disregarded. In the case of pure normal metals, in the weak spin-orbit interaction limit, the current can thus simply be expressed in terms of

$$\hat{j} = \hat{j}_0 + \hat{j}_{av};$$
 (14)

where the anom alous current simplies to

$$e\hat{j}_{av} = \frac{h}{6m D} ^{r} r_{c}$$
: (15)

The e ect of the spin-orbit interaction is consequently to induce a transverse spin Hall potential. The magnitude of the spin Hall e ect depends on the system size and geometry. If the system size is smaller than the spin-di usion length, a spin accumulation cannot build up within the system, and consequently the spin Hall e ect vanishes. Therefore, we consider the situation when the

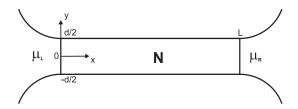


FIG. 3: The thin m etallic lm with a contact to reservoir.

system size is much larger than the spin-di usion length, L  $l_{\rm sf} = {}^{\rm h} \overline{D}_{\rm s}$ , where the total spin- ip relaxation time has contributions both due to spin-orbit scattering and magnetic impurity scattering, l= s= l= so + l= sm . The solution of the di usion equation is similar to the treatment in Ref. 9. At distances larger than the spin-di usion length from the reservoirs, the spin potential only depend on the transverse y-coordinate. In this regime, the general solution of the di usion equation (6) has the form

$$_{s} = c_{3}e^{y=l_{sf}} + c_{4}e^{y=l_{sf}};$$
 (16)

where  $c_3$  and  $c_4$  are constants to be determined. We can determine the constants  $c_3$  and  $c_4$  from the boundary condition that there is no particle or spin ow across the transverse boundaries, e.g. the 2 2 current in spin-space must satisfy:

$$\hat{J}_v(x;y=d=2)=0$$
: (17)

U sing the simplied equations (14) and (15) determining the current, we nd  $c_3$  and  $c_4$  and the spatially dependent transverse spin potential:

$$_{s;z}^{(A)}(y) = \frac{r}{\frac{3}{8}} \frac{r}{k_F L} \frac{r}{\frac{sm}{sm}} \frac{\sinh(y=l_{sf})}{\cosh(d=2l_{sf})}$$
: (18)

This expression exactly agrees with the result of Zhang  $_{\rm s;z}$  "  $^{\#}$  =  $l_{\rm sf}E_{\rm x}\,C_{\rm h}$ =C  $\sinh{(y=l_{\rm sf})}$ =cosh  $(d=2l_{\rm sf})$  when we insert the D rude conductivity C =  $e^2$  ( $k_{\rm F}$ )  $^3$ =6  $^2$ m, the anom alous H all conductivity C  $_{\rm h}$  =  $e^2$  ( $k_{\rm F}$ )  $^3$ =6  $^2$  (the dimensionless =  $_{\rm o}hk_{\rm F}^2$ ) and the electric eld in the x-direction E  $_{\rm x}$  = ( $_{\rm R}$   $_{\rm L}$ )=L . In addition, we use the identication between the spin-orbit spin- ip relaxation time and elastic scattering time, Eq. (7).

Formula (18) expresses the transverse spin Halle ect for thin metallic lms with small spin-orbit interaction. There are accumulation of spins directed perpendicular to the lm. As we see, the spin-Halle ect vanishes when scattering by magnetic impurities dominates the spin-orbit scattering, sm so, as expected. When magnetic impurity scattering is weak, and in the limit of a wider lm than the spin-diusion length d  $l_{\rm sf}$ , we make the observation that the magnitude of spin Halle ect is "universal", sH  $^{\rm (A)}_{\rm sH}$   $^{\rm (A)}_{\rm syz}$  (d=2):

$$_{\text{SH}}^{\text{(A)}} = \frac{\frac{1}{3}}{\frac{1}{2}} \frac{_{\text{R}} _{\text{L}}}{k_{\text{F}} L};$$
 (19)

e.g. the spin Hall voltage does not depend on the spin-orbit interaction constant . By "universal", we mean that the spin Hall potential does not depend on the strength of the spin-orbit scattering potential. This implies that, as long as the scattering of magnetic impurities is weak, light metals (e.g. Cu, Al) will give a similar spin Hall voltage as heavy metals (e.g. Pt). Note that the spin Hall potential depend on the Fermiwave vector of the metal,  $k_{\rm F}$ , and thus weakly depends on the type of normal metal through this dependence. The reason for the "universality" is that although the spin-Hall potential is proportional to the spin-orbit scattering it only builds up within the spin-di usion length which is inversely proportional to the spin-orbit scattering strength.

This section also illustrates the di erences between the extrinsic spin-orbit scattering o impurities in normalm etals, as treated here, and spin-orbit scattering induced by the Rashba term and impurities in the two-dimensional electron gas formed in semiconductor heterostructures. In the two-dimensional electron gas, there is currently a controversy whether the spin Hall conductivity can reach a universal value in dirty systems,  $_{\rm SH} = e=(8\ h)$ , independent of the spin-orbit scattering strength. In normal metals, we see from (15) that the spin Hall conductivity is not universal, but the spin Hall voltage (19) can be "universal" when scattering o magnetic impurities is weak.

# B. Thin metallic lm in tunneling contacts to ferrom agnet and norm alm etal.

We will now consider another transport regime, in which there is a nite spin-accumulation present in the normal metal even in the absence of spin-orbit scattering. The spin-accumulation can be achieved by sandwiching the normal metal between two ferrom agnets when the system is driven out of equilibrium, see Fig. 4. There are two extreme regimes depending on the ratio between the system length and the spin-diusion length. The rst regime, when the length is large, (L  $l_{\rm ef}$ ), does not provide novel physics since it is similar to the previous example. In this case any spins injected from the ferrom agnets will be lost, and the system resembles a pure normal

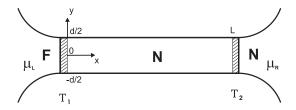


FIG .4: The thin m etallic  $\,$  lm  $\,$  with tunneling contacts  $T_1$  and  $T_2$  to ferrom agnet and norm alm etal.

m etal where a spin Hall voltage can build up transverse to the current direction. There is no charge Hall e ect produced by the spin-orbit interaction in the middle of the system in this case. Therefore, we consider the second, more interesting regime, when the normal metal is short, (L  $l_{\rm sf}$ ). In this case both spin and charge Hall potentials can build up transverse to the current direction governed by the spin-orbit scattering.

In addition, we need the boundary condition of the spin and charge ow through the tunnel contacts from the ferrom agnetic reservoirs into the normal metal wire. These boundary conditions follow from magnetoelectronic circuit theory, so that the interface transport can be described by spin-dependent conductances G and G for spin aligned and antialigned to the magnetization and a mixing conductance of rejection G for spins in the normal metal that are non-collinear to the magnetization direction. Form ost systems, ReG find G in G in

$$eI_{c} = (G'' + G^{\#}) \quad {}_{c}^{F} \quad {}_{c}(0;y) \quad (G'' \quad G^{\#})m \quad {}_{s}(0;y)$$
(20)

in term s of the local quasi-equilibrium chem ical potential in the ferrom agnet  $_{\rm c}^{\rm F}$  and the spin and charge chem ical potentials in the norm alm etal close to the ferrom agnetic interface  $_{\rm s}$  (x = 0;y) and  $_{\rm c}$  (x = 0;y). Here m is the m agnetization of the ferrom agnet (jm j= 1). For a tunnel contact 2R eG "# = G" + G#. $^{32}$  The spin-current along the transport, x, direction is then

$$eI_s = m [(G'' G^{\#})(G^{F} G^{G}) + (G'' + G^{\#})^{F}]$$
  
 $2R + (G'') + (G'' + G^{\#})^{F}$  (21)

We assume that the spin-orbit interaction is weak, and expand the charge and spin accumulations to  $% \left( 1\right) =\left( 1\right) +\left( 1\right)$ 

$$_{c}(x;y) = _{c}^{(0)}(x;y) + _{c}(x;y);$$
 (22)

$$_{s}(x;y) = _{s}^{(0)}(x;y) + _{s}(x;y);$$
 (23)

where the zeroth order terms are the charge and spin accumulations in the absence of spin-orbit interaction and

the corrections are caused by the spin-orbit interaction. First, we compute the zeroth order term sthat correspond to = 0. The boundary condition  ${}^{20}_{Jy} \, (x\,;y=-d=2)=0$  ofno current out of the transverse edges dictates that the general solutions  ${}^{(0)}_c$  and  ${}^{(0)}_s$  only vary in the transport direction:  ${}^{(0)}_c=c_0+c_1\frac{x}{L}$ ,  ${}^{(0)}_s=c_o+c_1\frac{x}{L}$ .

Now we can equate the current through the tunnel contact with the current in normal metal at x=0. This is a boundary condition on the ferrom agnet  $T_1$  (see Fig.4). For the charge current

$$G_{\circ}C_{1} = (G'' + G^{\sharp})(L_{\circ}G) (G'' G^{\sharp})m G$$
 (24)

where the conductance of the normal metal is  $G_{\circ}$  = wd=L, w is the width of the lm . For spin-current

$$G_0 c_1 = (G'' + G^{\#}) c_0 + m [(G'' G^{\#}) (L G): (25)]$$

At the norm alm etal-norm alm etal-tunnel contact  $T_2$  (see Fig.4) we use the same expressions for currents (20),(21) with G=G" =  $G^{\#}$ , and the boundary conditions are

$$G(c_0 + c_1) = G_0 c_1;$$
 (26)

$$G(c_0 + c_1) = G_0 c_1$$
: (27)

A fter straightforward calculations we nd

$$_{s}^{(0)}(x) = 1 \frac{G}{G + G_{o}} \frac{x}{L} \frac{G_{tot}^{"} G_{tot}^{\#}}{G_{tot}^{"} + G_{tot}^{\#}} (L_{R}) m;$$
(28)

$$_{c}^{(0)}(x) = c_{0} \frac{4}{G_{o}} \frac{1}{G_{tot}^{"}} + \frac{1}{G_{tot}^{"}} (L_{L}) \frac{x}{L};$$
 (29)

where the totale spin-dependent conductances of the system are given by the resistances in series 1=G  $_{\rm tot}^{"\,(\#)}$  = 1=G  $_{\rm o}^{"\,(\#)}$  + 1=G + 1=G  $_{\rm o}$ .  $c_0$  can be expressed similarly, but is not shown here since it does not govern the spin-orbit induced correction to the currents which will be considered next.

Next we introduce spin-orbit interaction which will produce current correction  $\hat{j}(x;y)$  so that the full current is expressed as  $\hat{j} = \hat{j}^0 + \hat{j}$ . The boundary condition  $\hat{j}_v(y = d=2) = 0$  gives

$$\frac{\theta}{\theta y} \quad c \quad \dot{y}_{r} = d=2 \quad = \quad \frac{h}{3m} \frac{\theta}{\theta x} \quad s;z \tag{30}$$

$$\frac{\varrho}{\varrho_{\mathbf{y}}} \quad s_{i\mathbf{x}} \quad \dot{\mathbf{j}}_{y=0} \quad d=2 \quad = \quad \frac{2}{3} \frac{\varrho}{\varrho_{\mathbf{x}}} \quad {}^{(0)} \quad s_{i\mathbf{y}}$$
 (31)

$$\frac{\varrho}{\varrho_{\mathbf{y}}} \quad _{\mathsf{s};\mathbf{y}} \quad \dot{\mathbf{y}}_{\mathsf{z}} = _{\mathsf{d}=2} \quad = \quad 2 \frac{\varrho}{\varrho_{\mathbf{x}}} \quad _{\mathsf{s};\mathbf{x}}^{(0)} \tag{32}$$

$$\frac{0}{0 \text{ gy}} \quad \text{s;z} \quad \dot{\mathbf{j}}_{y=} \quad d=2 \quad = \quad \frac{h}{3m \text{ D}} \quad \frac{0}{0 \text{ x}} \quad c^{(0)}$$
 (33)

where we have introduced the total polarization of the conductance of the system  $p_{tot}$   $(G_{tot}^{"} - G_{tot}^{\#}) = (G_{tot}^{"} + G_{tot}^{\#})$ . The derivative of x-component of the correction

to the spin potential is governed by side—jum p current, y-com ponent by skew scattering current and z-com ponent by anom alous current. In the lim it d  $\,$  L we can expand the corrections to the chem ical potentials in the sm all param eter (d=L), so that the solutions can be represented as

$$_{c} = {}^{(0)}_{c} + {}^{d}_{L} {}^{(1)}_{c}$$
 (34)

$$_{s} = {}^{(0)}_{s} + {\frac{d}{L}}_{s}$$
 (35)

Due to simpli ed di usion equations we write

$$c_{c}^{(i)} = c_{0}^{(i)} + c_{1}^{(i)} x + c_{2}^{(i)} y;$$
 (36)

$$c_{s}^{(i)} = c_{0}^{(i)} + c_{1}^{(i)} x + c_{2}^{(i)} y;$$
(37)

where i=0;1. We are interesting for  $\infty$  cients  $c_2^{(i)}$  and  $c_2^{(i)}$  because  $c_j^{(i)}$   $c_j$ =L,  $c_j^{(i)}$   $c_j$ ; j = 0;1. The boundary condition on the contact  $T_1$  gives

$$\frac{\theta}{\theta x} \quad c \quad \dot{\mathbf{j}}_{k=0} = \frac{G'' + G^{\#}}{G_{\circ}} \quad c (0; \mathbf{y}) + \frac{G'' \quad G^{\#}}{G_{\circ}} m \quad s (0; \mathbf{y}) = \frac{\theta}{\theta x} \quad s \quad \dot{\mathbf{j}}_{k=0} = \frac{G'' \quad G^{\#}}{G_{\circ}} \quad c (0; \mathbf{y}) + \frac{G'' + G^{\#}}{G_{\circ}} \quad s (0; \mathbf{y}) = \frac{4}{3} \frac{\theta}{\theta x} \quad s_{jx}^{(0)} e_{x};$$

and similarly for the contact  $T_2$ . If we consider these conditions for  $_{\rm C}=$   $_{\rm c}^{(0)}$ ,  $_{\rm s}=$   $_{\rm s}^{(0)}$  we derive  $c_2^{(0)}=$   $c_2^{(0)}=$  0. Conditions (30)-(33) give

$$\begin{split} c_2^{(1)} &= \frac{hm_z}{3m\,D} \frac{G\,\, p_{\text{tot}}}{G + G_o} \frac{L}{d} \\ c_{2;x}^{(1)} &= \frac{2}{3}m_y \frac{G\,\, p_{\text{tot}}}{G + G_o} \frac{L}{d} \\ c_{2;y}^{(1)} &= 2m_x \frac{G\,\, p_{\text{tot}}}{G + G_o} \frac{L}{d} \\ c_{2;z}^{(1)} &= \frac{h}{3m\,D} \frac{4}{G_o \, G_{\text{tot}}^{\text{"tot}} G_{\text{tot}}^{\text{\#}}}{G_{\text{tot}}^{\text{"tot}} G_{\text{tot}}^{\text{\#}}} \frac{L}{d}; \end{split}$$

Finally, we have for the spin-orbit induced charge Hall e ect

(B) 
$$(x;y)$$
  $m_z \frac{G p_{tot}}{G + G_0} \frac{L}{k_F L} \frac{y}{1};$  (38)

and for the spin Halle ect

$$_{\text{s;x}}^{\text{(B)}}(x;y)$$
  $\frac{2}{3} \text{ m }_{y} \frac{\text{L}}{\text{L}} \frac{\text{R}}{\text{G}} \frac{\text{G } p_{\text{tot}}}{\text{G + G}_{0}} y;$  (39)

$$_{\text{s;y}}^{\text{(B)}}(\mathbf{x};\mathbf{y}) \qquad 2 \text{ m }_{\mathbf{x}} \frac{\text{L}}{\text{I}} \frac{\text{R}}{\text{G}} \frac{\text{G p}_{\text{tot}}}{\text{G} + \text{G}} \mathbf{y}; \tag{40}$$

where listheelectron mean free path. As we see from the equation (38) the spin-orbit induced charge Halle ect is

non-zero only for nonzero m agnetization of the ferrom agnet in the z-direction (direction which is perpendicular to the lm). At the same time the spin-Halle ect of the spins along z, (41), is independent of the magnetization direction. So, assuming m = f0;0;1g the magnitude of Halle ect is

$$\frac{d}{d} \frac{G p_{\text{tot}}}{1 G + G_0} \frac{R}{k_F L};$$
(42)

and the spin Halle ect

The spin-orbit induced charge Halle ect vanishes when the polarization goes to zero, as should be expected. In comparison, we give the magnitude of spin Halle ect in pure normal metal regime in the  $\lim$  it of  $\lim$  lsf. As directly follows from eq. (18)

$$l_{sH}^{(A)} (d l_{sf}) = \frac{d}{l} \frac{R}{k_F L} :$$
 (44)

To evaluate the expressions (42), (43) and com pare them to (44) we assume the conductance at the tunnel barrier  $T_2$  equals to the sum of spin-dependent conductances at the barrier  $T_1$ , so  $G=G^{''}+G^{\#}$  and take a typical value of the polarization of the conductance of the system p (G  $^{''}-G^{\#})=(G^{''}+G^{\#})=1=2$ . The lim it  $G-G_0$  is not interesting because in this case our system will be similar to a pure normal metal attached to reservoirs, which was considered in the previous section. A nother lim it  $G-G_0$  is also less interesting due to the small induced voltage across the normal metal and consequently vanishing Hall e ects. So, we consider the most interesting case  $G=G_0$ . In this case

$$\frac{\frac{(B)}{sH}}{\frac{(A)}{sH}(d)} = \frac{3}{7};$$
 (45)

$$\frac{\frac{(B)}{H}}{\frac{(A)}{SH}(d l_{sf})} = \frac{1}{7}:$$
 (46)

W e see from these expressions that both the charge and the spin Halle ects are comparable to the spin Halle ffect in the pure normal metal regime attached to leads with perfect normal metal contacts in the regime Last last a lithough the magnitudes of charge and spin Halle ects have a similar structure in both regimes, they have a different origin in principle. The ects in this section are due to skew scattering, side-jump scattering and anomaloys velocity, while the ects in the previous section are due to the anomalous velocity operator only. We treated in this section the regimed L.We expect that the spin Halland the charge Halle ects increase their magnitudes  $_{\rm H}^{\rm (B)}$  and  $_{\rm SH}^{\rm (B)}$  with increasing of duntil saturation when dast similary to the case when the spin Halle ect in pure normal metal attains the "universal value" (19).

# IV. M ICROSCOPIC DERIVATION OF DIFFUSION EQUATION

We will in this section derive the diusion equations rigorously from the microscopoic H am iltonian with the Keldysh G reen's function technique in the quasiclassical limit. The nonmagnetic impurity potential (2) in terms of incident k and scattered  $k^0$  wave vectors is  $V_{im\,p}\,(k\,;k^0)={}_{i\ i}\exp{i\ k}\,k^0)\,r_i$ . Consequently, the spin-orbit interaction in this representation is  $\hat{V}_{so}\,(k\,;k^0)={}_{i\ (=k_F^2)^{\wedge}}\,(k\,{}^0\!k\!V_{im\,p}\,(k\,{}^{\phantom{i}}\,k^0)$ . Thus, in normal metals with dilute in purities the electrons interact with the potential  $V\,(k\,;k^0)$ 

$$\hat{V}(k;k^{0}) = \hat{M}V_{imp}(k;k^{0});$$
 (47)

where we have introduced the 2 2 m atrix in spin-space

$$\hat{M} \hat{1} = \frac{1}{k_{E}^{2}} \hat{k} (k + k^{0}) :$$
(48)

In addition, the electrons interact with magnetic in purities (4) to be discussed below. Our transport theory is based on the Keldysh form alism  $^{30,33}$ . In this form alism the G reen's function has the form

$$G = \begin{pmatrix} \hat{G}^{R} & \hat{G}^{K} \\ 0 & \hat{G}^{A} \end{pmatrix} ; \tag{49}$$

where the retarded, advanced and Keldysh Green's functions are

$$\hat{G}^{R} = i (t_1 t_2)h[(x_1); (x_2)]_{+}i;$$
 (50)

$$\hat{G}^{A} = +i (t_{2} t_{1})h[(x_{1}); (x_{2})]+i;$$
 (51)

$$\hat{G}^{K} = ih[(x_1); (x_2)] i:$$
 (52)

Here is the ferm ion annihilation operator,  $^+$  is the ferm ion creation operator, both in the Heisenberg picture, and the coordinate  $x_i$  denotes both spatial position and time,  $x_i = (x_i; t_i)$ . Note that the ferm ion annihilation and creation operators are 2-component vectors in spin-space. The self-energy has the same triangular matrix structure as the G reen's function,

$$= \begin{array}{cccc} {}^{\wedge_{R}} {}^{\wedge_{K}} \\ {}^{\wedge_{A}} \end{array} : \tag{53}$$

We denote 4 4 m atrices in Keldysh space by the symbol "check" () and 2 2 m atrices in spin space by the symbel "hat" (). Next we denote the center-of-mass and relative variables  $x=\frac{1}{2}(x_1+x_2)$ ;  $r=x_1-x_2$ , and Fourier transform with respect to the relative coordinate r in order to obtain the G reen's function in the mixed representation

$$Z$$
  $G(p;x) = dre^{ip} \ddot{G}(x + r=2;x r=2):$  (54)

We will also use the -integrated (quasiclassical) Green's function g(n;r) = (i=) d G(p;r), where  $= p^2 = 2m$ 

, and n is a unit vector along the momentum at the Ferm i surface (n =  $k_F = j_{k_F} j$ ). Let us rst consider the current produced by the normal velocity operator of the electrons,  $j_N$ . This current is expressed as  $j_N = (e=m) < h^+ p$  i, where p is the momentum operator. Introducing the G reen's functions, the current due to the normal velocity operator is

$$\hat{J}_{N}(x_{1}) = \frac{e}{2m} \lim_{x_{1}! x_{2}} (r_{1} r_{2}) \hat{G}^{K}(x_{1}; x_{2}) i:$$
 (55)

Inserting the Fourier representation of the G reen's function in the quasiclassical approximation gives for the ordinary current in the mixed representation<sup>30</sup>

$$\hat{J}_{N} = \frac{eN_{o}}{2}^{Z} d^{"} \frac{dn}{4} v_{F} n \hat{g}^{K} (n;r) ; \qquad (56)$$

where h::i denotes averaging over impurities and N  $_{\circ}$  is the density of states at the Ferm i level.

The total current also has contributions caused by the anom alous velocity operator. This contribution to the current can be expressed  $^{30,34}$  as

$$\hat{J}_{av} = \frac{eN_o}{2}^{Z} d^{"} \frac{d}{4} \frac{dn^0}{4} h \hat{v}_{so} (n; n^0) g (n^0; r) i^{K} : (57)$$

The anomalous current caused by the spin-orbit interaction is

$$\hat{v}_{so}\left(\mathbf{r}\right) = \frac{dV_{so}\left(\mathbf{r}\right)}{dp} = \frac{1}{hk_{F}^{2}} \cdot r V_{imp}\left(\mathbf{r}\right); \quad (58)$$

In Fourier space,

where we have introduced the 2 2 m atrix in spin-space

$$\hat{N}$$
  $\frac{1}{hk_E}$   $\hat{k}$   $k^0$  : (60)

The challenge is now to nd the average,  $h\hat{v}_{so}$  (n;n<sup>0</sup>)gi. Note that this is different than the average G reen's function appearing in the contribution from the normal velocity operator (56). In the anomalous current (58), a product of the spin-orbit scattering potential and the G reen's function, both of which depends on the impurity conguration has to be evaluated, and in general one should expect that  $h\hat{v}_{so}$ gié  $h\hat{v}_{so}$ ihgi. U sing the D year equation  $hgi = g_0 + g_0$  hgi and  $h\hat{v}_{so}$ gi =  $h\hat{v}_{so}$ 1  $\hat{v}_{so}$ 1  $\hat{v}_{so}$ 2 we not the result

$$hv_{so}gi = \hat{N}\hat{M}^{1} hgi:$$
 (61)

The self-energy part  $\hat{D}$  can be expressed in the Born approximation as  $\hat{D}$  and has one contribution due to scattering o non-magnetic impurties and two

contributions due to the spin-orbit interaction, (n) =  $_{i}(n) + _{\infty}^{(1)}(n) + _{\infty}^{(2)}(n) + _{\infty}^{(2)}(n) + _{\infty}^{(n)}(n)$ , where

$$_{i} = \frac{ih}{2} hg (n^{0}) i_{n^{0}};$$
 (62)

$$\sum_{\infty}^{(2)} = \frac{ih^{-2}}{2} h^{\wedge} (n - n^{0}) g (n^{0})^{\wedge} (n - n^{0}) \dot{1}_{n^{0}}$$
 (63)

$$_{\infty}^{(1)} = \frac{h}{2} hg (n^{0})^{n} (n n^{0}) + h \pi i_{n^{0}} :$$
 (64)

Scattering by magnetic impurities (4) do not cause additional terms in the expressions for the current density, but gives an additional contribution the the electron self-energy

$$_{sm} = \frac{ih}{2 _{sm}} \frac{1}{3} \frac{X}{3} _{i} _{j} hg (n^{0}) i_{h^{0}} _{i};$$
 (65)

where the spin- ip relaxation time due to magnetic impurity scattering is

$$\frac{1}{sm} = \frac{8}{3} n_{sm} N_{o} S (S + 1)^{Z} \frac{dn^{0}}{4} \dot{y}_{sm} (n n^{0})^{2}; (66)$$

 $n_{\text{sm}}$  is the concentration of the magnetic impurities and S is the quantum spin number of the impurity. The

self-energy due to scattering o magnetic in purities will leads to simple additional spin- ip relaxation terms in the spin di usion equation. In normal metals, the retarded component of G reen's function equals  $\hat{g}^R = \hat{1}$ , and  $\hat{g}^A = \hat{g}^R = \hat{1}$ . By evaluating the Keldysh component Eq. (61) the anomomalous current is given as

$$\hat{j}_{av} = \frac{\frac{ieN_oh}{8}}{8}^R d^{\bullet} \frac{R}{4} \frac{d^{\bullet} d^{\bullet}}{4} \hat{N} \hat{M}^{\bullet} \frac{1}{4} [(2 + 2)\hat{g}^{K} (n^{0}) + 2^{\bullet} (n^{0})\hat{g}^{K} (n^{0}) \hat{n} n^{0}) + \hat{g}^{K} (n^{0})\hat{g}^{K} (n^{0$$

W e consider transport in the di use transport regim e. In the di usive regim e, characterized by  $v_F$  L (L is the system size) the G reen's function is almost isotropic<sup>30</sup>, and we can then expand the G reen's function in form of isotropic and nonisotropic parts,

Z 
$$d^{"}g^{K}(r;n) = ^{\circ}(r) + \hat{j_{1}}(r) n :$$
 (68)

A fter integrating of the formula (67) we have the result

where Tr(:::) denotes the sum of diagonal elements of a matrix and the spin-orbit interaction strength dependent functions  $f_i()$  are

$$f_1 = + \frac{2}{9} + (1 - 2)^{\frac{Z}{2}} \frac{(n_z^0)^2 - (n_z)^2 (n_x^0)^2}{1 + 2 \dot{j}_1 - n_z^0} \frac{dn}{4} \frac{dn}{4}$$
 (70)

$$f_{2} = \frac{2}{9} + 2^{2} \frac{2 (n_{i})^{2} (n_{j}^{0})^{2} (n_{k}^{0})^{2} (n_{k})^{2} (n_{j}^{0})^{2}}{1 + 2 \dot{n} n^{0} \dot{f}} \frac{dn}{4} \frac{dn^{0}}{4}$$
(71)

$$f_{3} = \frac{2}{3} + 2 \frac{Z (n_{i})^{2} (n_{k}^{0})^{4} + Z^{2} (n_{k})^{2} (n_{i}^{0})^{2} (n_{k}^{0})^{2} (n_{k}^{0})^{2}}{1 + \frac{2}{n} n^{0}} \frac{(n_{k}^{0})^{2} (n_{k}^{0})^{2}}{4} \frac{dn}{4}$$
(72)

In the lim it of weak spin-orbit interaction ( 1) we thus not the current contribution due to the anomalous veloicty operator

$$\hat{J}_{av} = \frac{eN_o}{8 k_F} \hat{J}_1 ^{\uparrow} ^{\uparrow} \hat{J}_1$$
 (73)

We have now found the full expression for the current density in terms of the distribution functions and we will now proceed to compute the di usion equation. The starting point in calculating the Green's function is the equation of motion for the impurity averaged quasiclas-

sical G reen's function, the E ilenberger equation.

$$hv_F r hgi + i ; hgi = 0;$$
 (74)

where  $v_F$  is Ferm y velosity. We will in the following om it the impurity average symbol and only implicity write averaging over momentum  $\hat{k}$  or  $\hat{k}^0$ . We calculate Keldysh components of the various self-energy commutators. For scattering on non-magnetic impurities we obtain the well-known result:

$$i \quad _{i}; g^{K} = \frac{h}{f} \quad \mathring{g}^{K} \qquad \mathring{g}^{K} \qquad (75)$$

For spin-orbit scattering, which gives rise to side-jump and skew-skattering, using  $h^{(n)} (n n^0)^{(n)} = \hat{1}$ we nd

$${}^{\land (2)R}_{SO} = \frac{ih^{2}}{2} \hat{1}; \quad {}^{\land (2)A}_{SO} = \frac{ih^{2}}{2} \hat{1}$$
 (76)

and

Sim ilarly, using  $h^{n}$  (n  $n^{0}$ ) i = 0, we nd  $n^{n}$  i = 0 i = 0

In the di usive transport regim e, we use the representation

$$^{\circ}_{\circ} = {}_{\circ}\hat{1} + {}_{s}^{\circ} : \qquad (79)$$

Employing (76), we not after averaging overm omentum, the expression for  $\hat{s}_{so}$  id  $\hat{d}_{so}$  if  $\hat{d}_{so}$ ; g, where  $\hat{d}_{so}$  is the energy spectrum of the system:

Sim ilarly, for magnetic impurity scattering, from (65) we

$$^{\text{R}}_{\text{sm}} = \frac{\text{ih}}{2 - n} \hat{1}; \quad ^{\text{A}}_{\text{sm}} = \frac{\text{ih}}{2 - n} \hat{1}; \quad (82)$$

$$^{^{\wedge}K}_{sm} = \frac{ih}{2_{sm}} c\hat{1} s^{^{\wedge}}; \qquad (83)$$

and

$$^{\circ}_{sm} = \frac{h}{sm} s^{\circ} + \frac{h}{2sm} j_1 n :$$
 (84)

After substitution of (75), (81), (80), (84) into Eilenberger equation (74) and averaging over dn we nd

$$\frac{1}{3}v_F r \hat{j}_1 + \frac{8^2}{9} + \frac{1}{sm} s^2 = 0$$
: (85)

Next, we nd a second equation by averaging over dn the (74) multiplated by n

$$v_{\tilde{h}} r ^{\circ} + (1 + \frac{2^{2}}{3}) \hat{j}_{1} + \frac{1}{3} (\hat{j}_{1} ^{\circ}) + (^{\circ} \hat{j}_{1}) = 0 :$$
 (86)

$$\hat{J}_{1} = V_{F} \left[ \frac{1}{1+2^{2}=3} r _{0} + K_{1} r _{s} \right] K_{2} (^{r}) _{s} + (K_{2} K_{1}) (r _{s});$$
(87)

$$K_1 = \frac{4^2}{(3+2^2)^2 - 4^2}; (88)$$

$$K_2 = \frac{2 (3+2^2)}{(3+2^2)^2 4^2}$$
: (89)

We now use the representation (68) to nd from (56) the current caused by the normal velocity operator

$$\hat{J}_{N}(r) = \frac{eN_{o}}{2}^{Z} \frac{dn}{4} v_{F} n (^{\circ}_{o} + \hat{J}_{1} n) = \frac{eN_{o} v_{F}}{6} \hat{J}_{1} : (90)$$

A fter substitution (87) into equation above we nd nally that there are three contributions to the current density from the normal velocity operator:

$$\hat{j}_N(\mathbf{r}) = \hat{j}_O(\mathbf{r}) + \hat{j}_{Si}(\mathbf{r}) + \hat{j}_{SS}(\mathbf{r})$$

where

$$\hat{j}_{sj} = \frac{(3+2^{-2})eN_oD}{(3+2^{-2})^2 4^2} (^r)_s$$
 (92)

$$\hat{J}_{ss} = \frac{eN_oD}{2^2 + 2 + 1} (r_s)$$
 (93)

A lso using expression for  $\hat{j_1}$  (87) we can rewrite the formula for anom alous current (69) like

$$\hat{j}_{av}(r) = \frac{eN_{o}v_{F}}{4k_{F}} f \frac{2^{2}}{2^{2}+2+1} r \qquad _{s} + ^{r} r_{c} f_{1}() + P P_{i}e_{i} p_{jk} ijk [(K_{1}()f_{2}() K_{2}()f_{3}()) r_{k} p_{s;j} + (K_{1}()f_{3}() K_{2}()f_{2}()) r_{j} p_{s;k}]g$$
(94)

after substitution (87):

$$r^2_{C} = 0$$
 (95)

$$\frac{(2^{2}+3)^{2}D}{(2^{2}+3)^{2}}r^{2} = \frac{s}{so} + \frac{4^{2}D}{(2^{2}+3)^{2}}r (r s)$$
(96)

In the lim it of weak spin-orbit interaction ( 1) we obtain the simplified diffusion equations (5) and (6) and the simplified expression for the current density (9), (10), (11), (12), and (13).

#### V. CONCLUSIONS

We have derived di usion equations for spin and charge ow in normal metals and the associated expression for the spin and charge currents. The total current consists of four contributions: Ordinary current, anomalous current, side-jump current and skew scattering current. These macroscopic di usion equations, allows computation of charge Hall voltages and spin Hall voltages in pure normal metals or hybrid ferromagnet-normal metal systems.

We have considered two experimental relevant geometries and calculated Hall and spin-Hall voltages in the case of weak spin-orbit interaction. In pure normal metals with no ferrom agnetic contacts, there is no charge

Halle ect due to the spin-orbit interaction, and the spin Halle ect is caused by the anom alous current, in agreement with the observation in Ref. 9. In this geometry, we have made the additional observation that the spin Hall voltage reaches and "universal" value independent of the strength of the spin-orbit interaction, when spin-ip scattering due to spin-orbit scattering dom inates spin-ip scattering due to magnetic impurities. When a spin-polarized current is injected into a normal metal lm, both a Hall voltage and a spin Hall voltage exist. The magnitude of the Hall voltage is governed by sidejum p, skew scattering and anom alous currents when the system is shorter than the spin-di usion length. For systems longer than the spin-di usion length, the Hallvoltage vanishes, and the spin Halle ect resum es the value dom inated by the anom alous current. In the interm ediate regime, the competition between skew scattering, side-jum p scattering and anom alous velocity operator determ ines the spin Halland charge Hall voltages.

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